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NTMFS4833N

MOSFET – Power, Single, N-Channel, SO-8FL 30 V, 191 A

Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

Applications

- Refer to Application Note AND8195/D
- CPU Power Delivery
- DC-DC Converters
- Low Side Switching

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		V_{DS}	30	V
Gate-to-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	I_D	28	A
	$T_A = 85^\circ\text{C}$		20.5	
Power Dissipation $R_{\theta JA}$ (Note 1)	$T_A = 25^\circ\text{C}$	P_D	2.7	W
Continuous Drain Current $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	I_D	16	A
	$T_A = 85^\circ\text{C}$		12	
Power Dissipation $R_{\theta JA}$ (Note 2)	$T_A = 25^\circ\text{C}$	P_D	1.1	W
Continuous Drain Current $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	I_D	191	A
	$T_C = 85^\circ\text{C}$		138	
Power Dissipation $R_{\theta JC}$ (Note 1)	$T_C = 25^\circ\text{C}$	P_D	113.6	W
Pulsed Drain Current	$T_A = 25^\circ\text{C}$, $t_p = 10 \mu\text{s}$	I_{DM}	288	A
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)		I_S	104	A
Drain to Source dV/dt		dV/dt	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy ($T_J = 25^\circ\text{C}$, $V_{DD} = 30 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_L = 35 \text{ A}_{pk}$, $L = 1.0 \text{ mH}$, $R_G = 25 \Omega$)		EAS	612.5	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

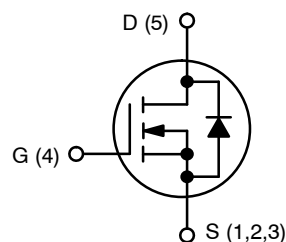
1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.



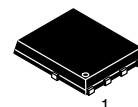
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$V_{(BR)DS}$	$R_{DS(on)}$ MAX	I_D MAX
30 V	2.0 m Ω @ 10 V	191 A
	3.0 m Ω @ 4.5 V	

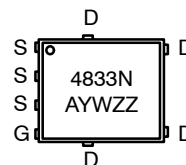


N-CHANNEL MOSFET



SO-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4833NT1G	SO-8FL (Pb-Free)	1500/Tape & Reel
NTMFS4833NT3G	SO-8FL (Pb-Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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2. Surface-mounted on FR4 board using the minimum recommended pad size.
(Cu area = 50 mm² [1 oz])

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	1.1	°C/W
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	45.6	
Junction-to-Ambient – $t < 10s$ (Note 3)	$R_{\theta JA}$	17.1	
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	117.4	

3. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size. (Cu area = 50 mm² [1 oz])

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			17		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$	$T_J = 25^\circ\text{C}$		1	μA
			$T_J = 125^\circ\text{C}$		10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	1.5		2.5	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			7.12		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V to } 11.5\text{ V}$	$I_D = 30\text{ A}$	1.3	2.0	m Ω
			$I_D = 15\text{ A}$	1.3		
		$V_{GS} = 4.5\text{ V}$	$I_D = 30\text{ A}$	2.3	3.0	
			$I_D = 15\text{ A}$	2.3		
Forward Transconductance	g_{FS}	$V_{DS} = 15\text{ V}, I_D = 15\text{ A}$		30		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 12\text{ V}$		5600		pF
Output Capacitance	C_{OSS}			1200		
Reverse Transfer Capacitance	C_{RSS}			650		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		39	58	nC
Threshold Gate Charge	$Q_{G(TH)}$			6.0		
Gate-to-Source Charge	Q_{GS}			16		
Gate-to-Drain Charge	Q_{GD}			17		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$		88		nC

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		25		ns
Rise Time	t_r			34		
Turn-Off Delay Time	$t_{d(OFF)}$			35		
Fall Time	t_f			17		
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = 11.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$		14		ns
Rise Time	t_r			19		
Turn-Off Delay Time	$t_{d(OFF)}$			50		
Fall Time	t_f			10		

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 30 A	T _J = 25°C	–	0.8	1.0	V
			T _J = 125°C	–	0.68	–	
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 30 A		–	38	–	ns
Charge Time	t _a			–	19	–	
Discharge Time	t _b			–	19	–	
Reverse Recovery Charge	Q _{RR}			–	36	–	

PACKAGE PARASITIC VALUES

Source Inductance	L_S	$T_A = 25^\circ\text{C}$	–	0.50	–	nH
Drain Inductance	L_D		–	0.005	–	nH
Gate Inductance	L_G		–	1.84	–	nH
Gate Resistance	R_G		–	1.0	–	Ω

- Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

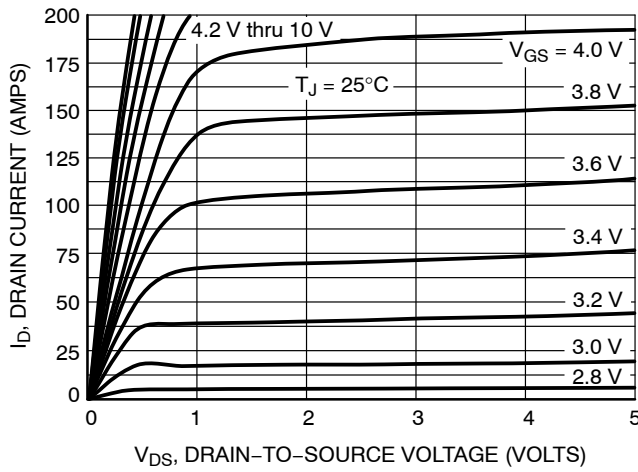


Figure 1. On-Region Characteristics

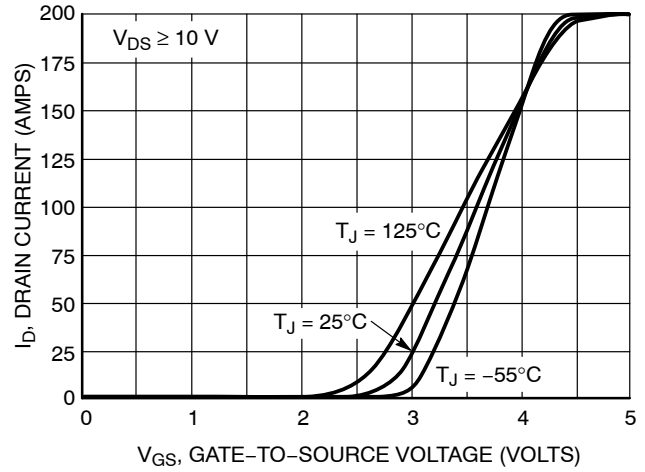


Figure 2. Transfer Characteristics

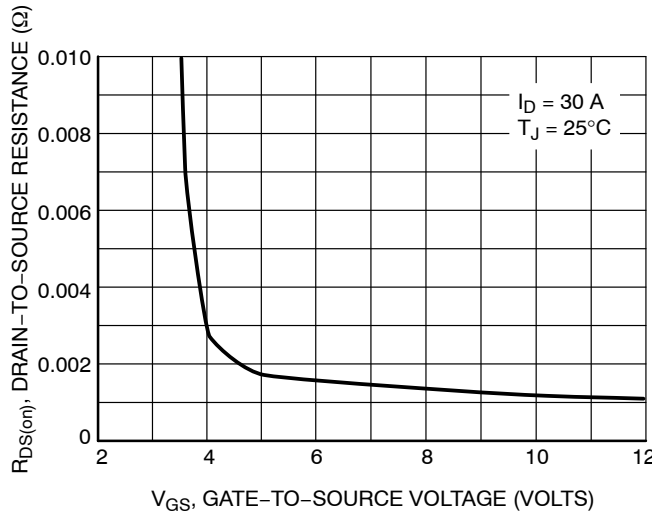


Figure 3. On-Resistance vs. Gate-to-Source Voltage

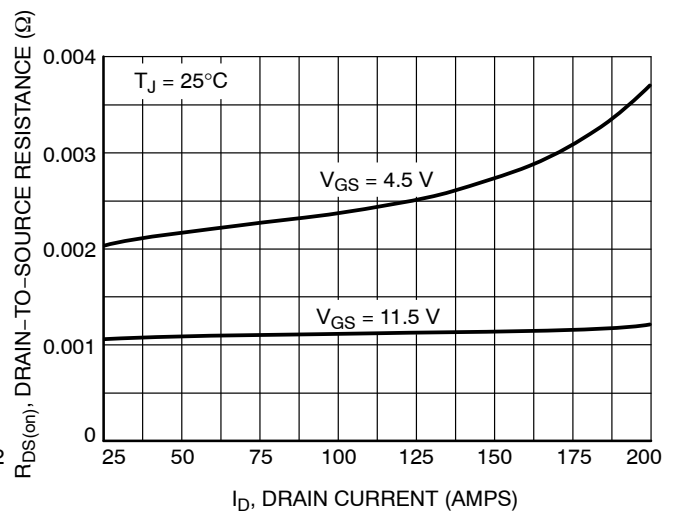


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

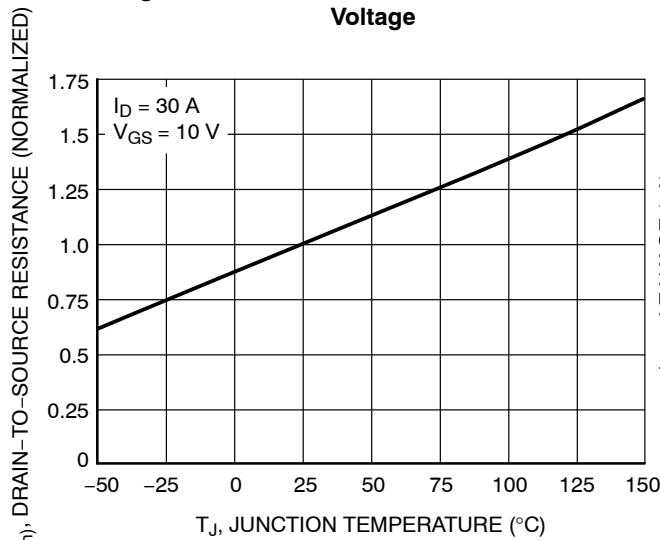


Figure 5. On-Resistance Variation with Temperature

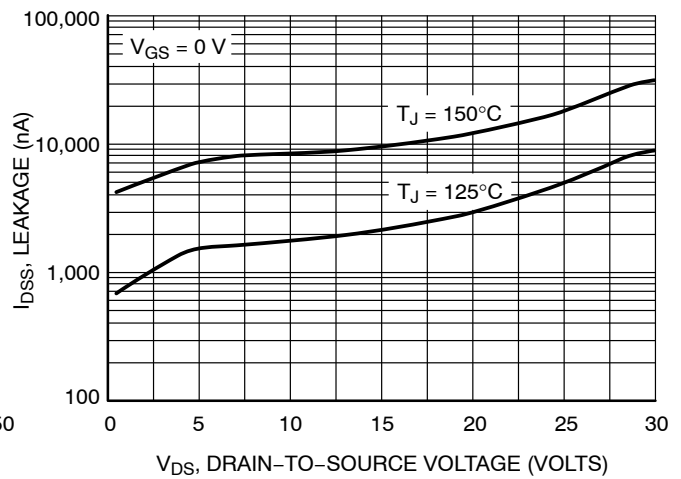
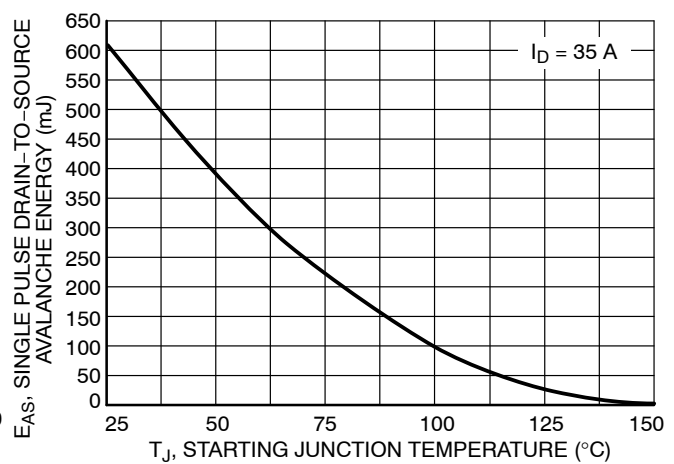
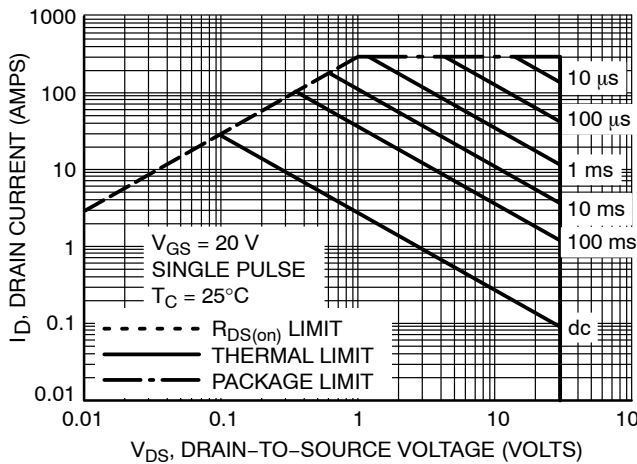
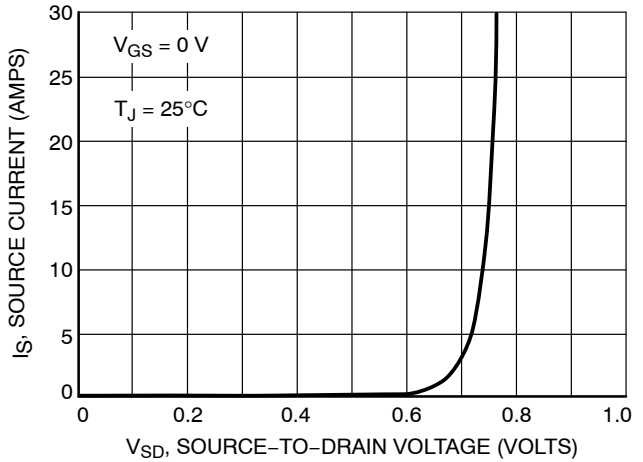
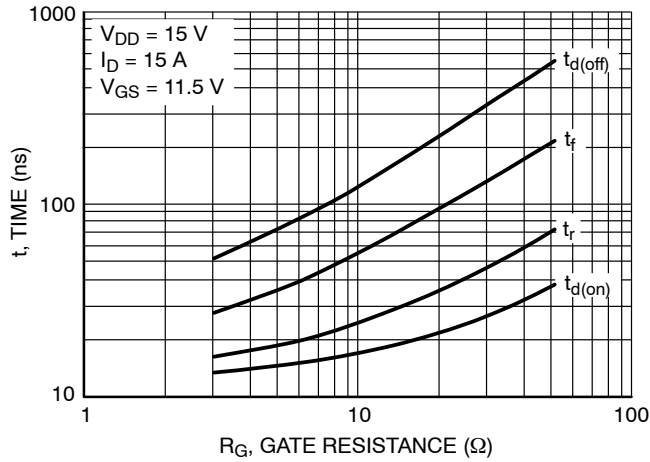
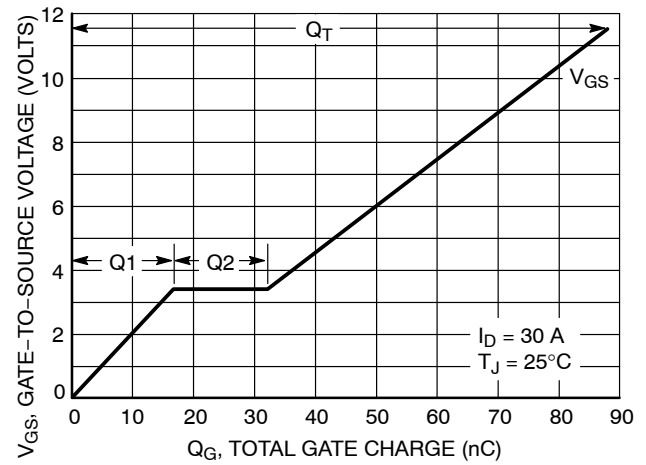
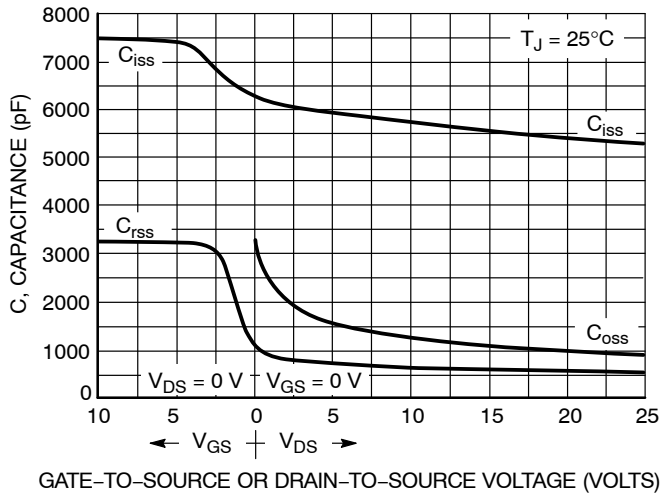


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES



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TYPICAL PERFORMANCE CURVES

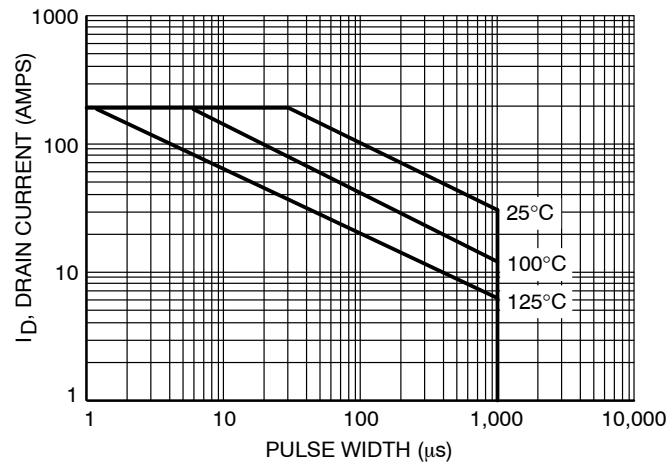


Figure 13. Avalanche Characteristics

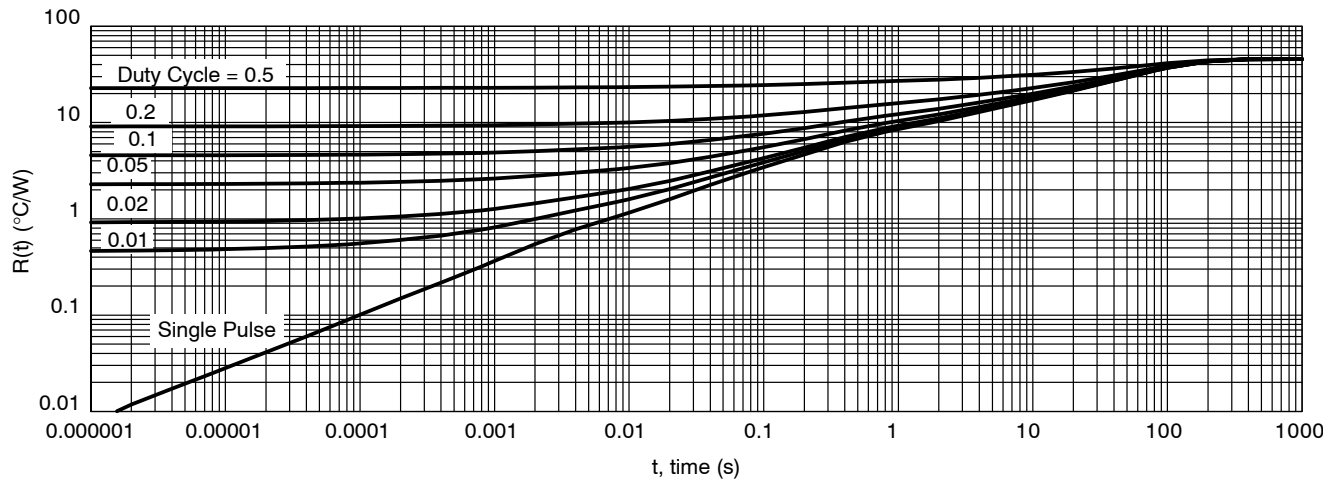
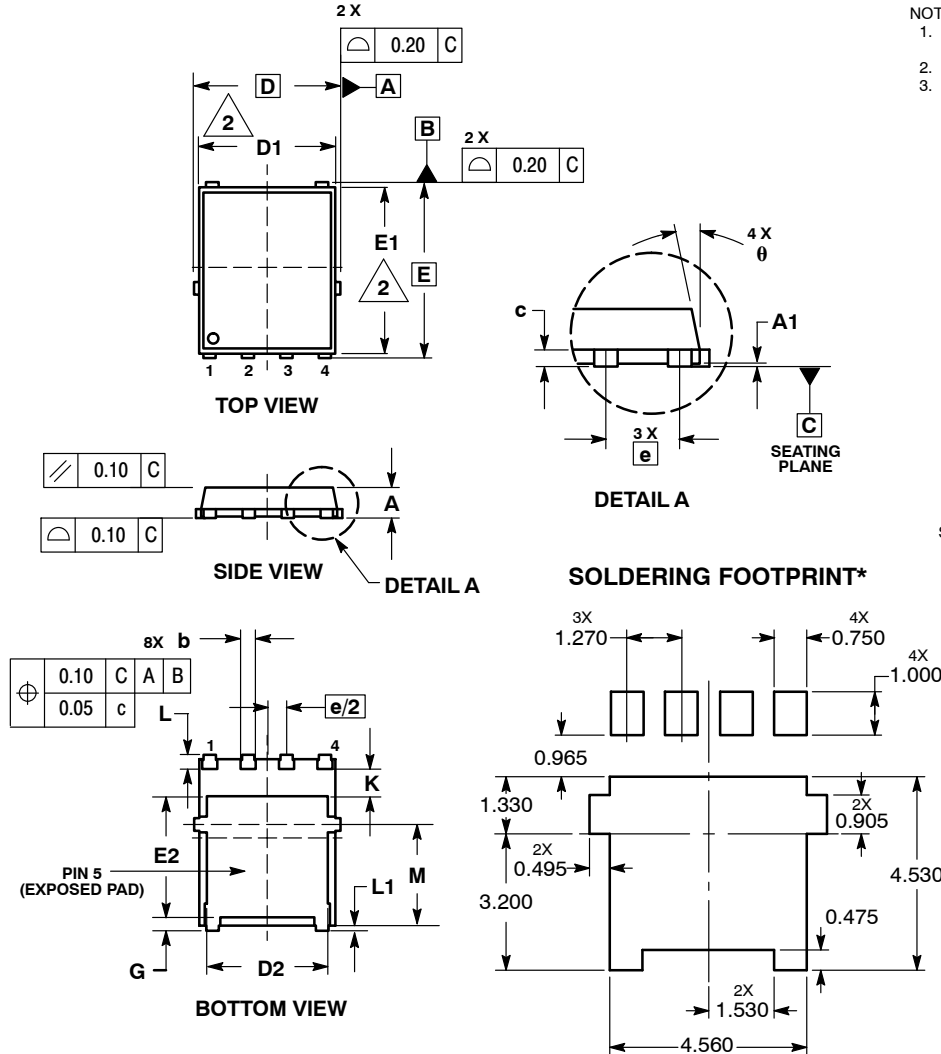


Figure 14. FET Thermal Response

NTMFS4833N

PACKAGE DIMENSIONS

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE G



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.50	4.90	5.10
D2	3.50	---	4.22
E	6.15 BSC		
E1	5.50	5.80	6.10
E2	3.45	---	4.30
e	1.27 BSC		
G	0.51	0.61	0.71
K	1.20	1.35	1.50
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0°	---	12°

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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